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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101phdfa-v0

Table 1-1. List of Ordering Part Numbers

(4/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
44 pins	44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)	Mounted	A	R5F100FAAFP#V0, R5F100FCAFP#V0, R5F100FDAFP#V0, R5F100FEAFP#V0, R5F100FFAFP#V0, R5F100FGAFP#V0, R5F100FHAFP#V0, R5F100FJAFP#V0, R5F100FKAFP#V0, R5F100FLAFP#V0 R5F100FAAFP#X0, R5F100FCAFP#X0, R5F100FDAFP#X0, R5F100FEAFP#X0, R5F100FFAFP#X0, R5F100FGAFP#X0, R5F100FHAFP#X0, R5F100FJAFP#X0, R5F100FKAFP#X0, R5F100FLAFP#X0
			D	R5F100FADFP#V0, R5F100FCDFP#V0, R5F100FDDFP#V0, R5F100FEDFP#V0, R5F100FFDFP#V0, R5F100FGDFP#V0, R5F100FHDFP#V0, R5F100FJDFP#V0, R5F100FKDFP#V0, R5F100FLDFP#V0 R5F100FADFP#X0, R5F100FCDFP#X0, R5F100FDDFP#X0, R5F100FEDFP#X0, R5F100FFDFP#X0, R5F100FGDFP#X0, R5F100FHDFP#X0, R5F100FJDFP#X0, R5F100FKDFP#X0, R5F100FLDFP#X0
			G	R5F100FAGFP#V0, R5F100FCGFP#V0, R5F100FDGFP#V0, R5F100FEGFP#V0, R5F100FFGFP#V0, R5F100FGGFP#V0, R5F100FHGFP#V0, R5F100FJGFP#V0 R5F100FAGFP#X0, R5F100FCGFP#X0, R5F100FDGFP#X0, R5F100FEGFP#X0, R5F100FFGFP#X0, R5F100FGGFP#X0, R5F100FHGFP#X0, R5F100FJGFP#X0
		Not mounted	A	R5F101FAAFP#V0, R5F101FCAFP#V0, R5F101FDAFP#V0, R5F101FEAFP#V0, R5F101FFAFP#V0, R5F101FGAFP#V0, R5F101FHAFP#V0, R5F101FJAFP#V0, R5F101FKAFP#V0, R5F101FLAFP#V0 R5F101FAAFP#X0, R5F101FCAFP#X0, R5F101FDAFP#X0, R5F101FEAFP#X0, R5F101FFAFP#X0, R5F101FGAFP#X0, R5F101FHAFP#X0, R5F101FJAFP#X0, R5F101FKAFP#X0, R5F101FLAFP#X0
			D	R5F101FADFP#V0, R5F101FCDFP#V0, R5F101FDDFP#V0, R5F101FEDFP#V0, R5F101FFDFP#V0, R5F101FGDFP#V0, R5F101FHDFP#V0, R5F101FJDFP#V0, R5F101FKDFP#V0, R5F101FLDFP#V0 R5F101FADFP#X0, R5F101FCDFP#X0, R5F101FDDFP#X0, R5F101FEDFP#X0, R5F101FFDFP#X0, R5F101FGDFP#X0, R5F101FHDFP#X0, R5F101FJDFP#X0, R5F101FKDFP#X0, R5F101FLDFP#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(5/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0, R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0, R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0, R5F100GLAFB#V0 R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0, R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0, R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0, R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0, R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0, R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0, R5F100GLDFB#V0 R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0, R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0, R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0, R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0, R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0, R5F100GHGFB#V0, R5F100GJGFB#V0 R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0, R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0, R5F100GHGFB#X0, R5F100GJGFB#X0
		Not mounted	A	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0, R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0, R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0, R5F101GLAFB#V0 R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0, R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0, R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0, R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0, R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0, R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0, R5F101GLDFB#V0 R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0, R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0, R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0, R5F101GLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

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Table 1-1. List of Ordering Part Numbers

(9/12)

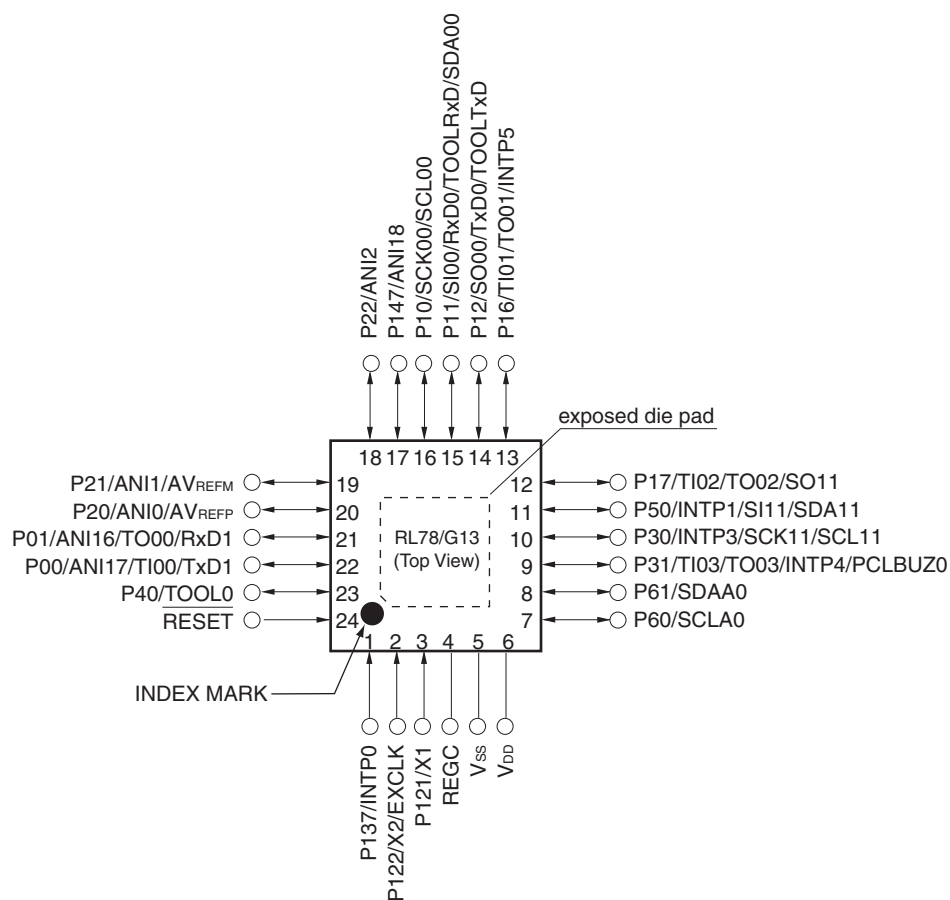
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LLAFB#V0 R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LGAFB#X0, R5F100LHAFB#X0, R5F100LJAFB#X0, R5F100LKAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDDB#V0, R5F100LGDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LKDFB#V0, R5F100LLDFB#V0 R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDDB#X0, R5F100LGDFB#X0, R5F100LHDFB#X0, R5F100LJDFB#X0, R5F100LKDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0 R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
	64-pin plastic VFGBGA (4 × 4 mm, 0.4 mm pitch)	Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LLAFB#V0 R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0, R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0
			D	R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDDB#V0, R5F101LGDFB#V0, R5F101LHDFB#V0, R5F101LJDFB#V0, R5F101LKDFB#V0, R5F101LLDFB#V0 R5F101LCDFB#X0, R5F101LDDFB#X0, R5F101LEDFB#X0, R5F101LFDDB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
		Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0
			G	R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0 R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
		Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.2 24-pin products

- 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



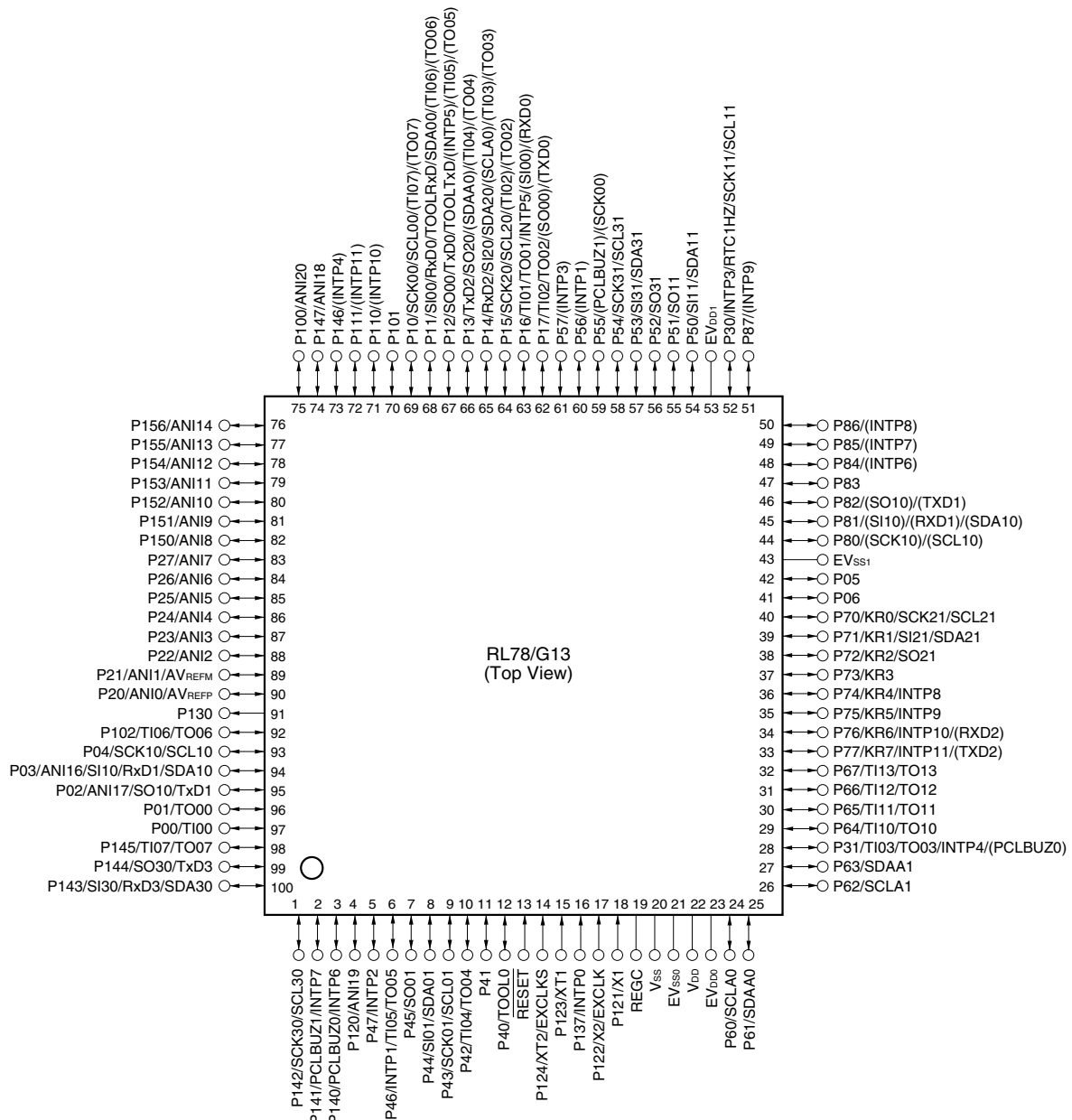
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to Vss.

1.3.13 100-pin products

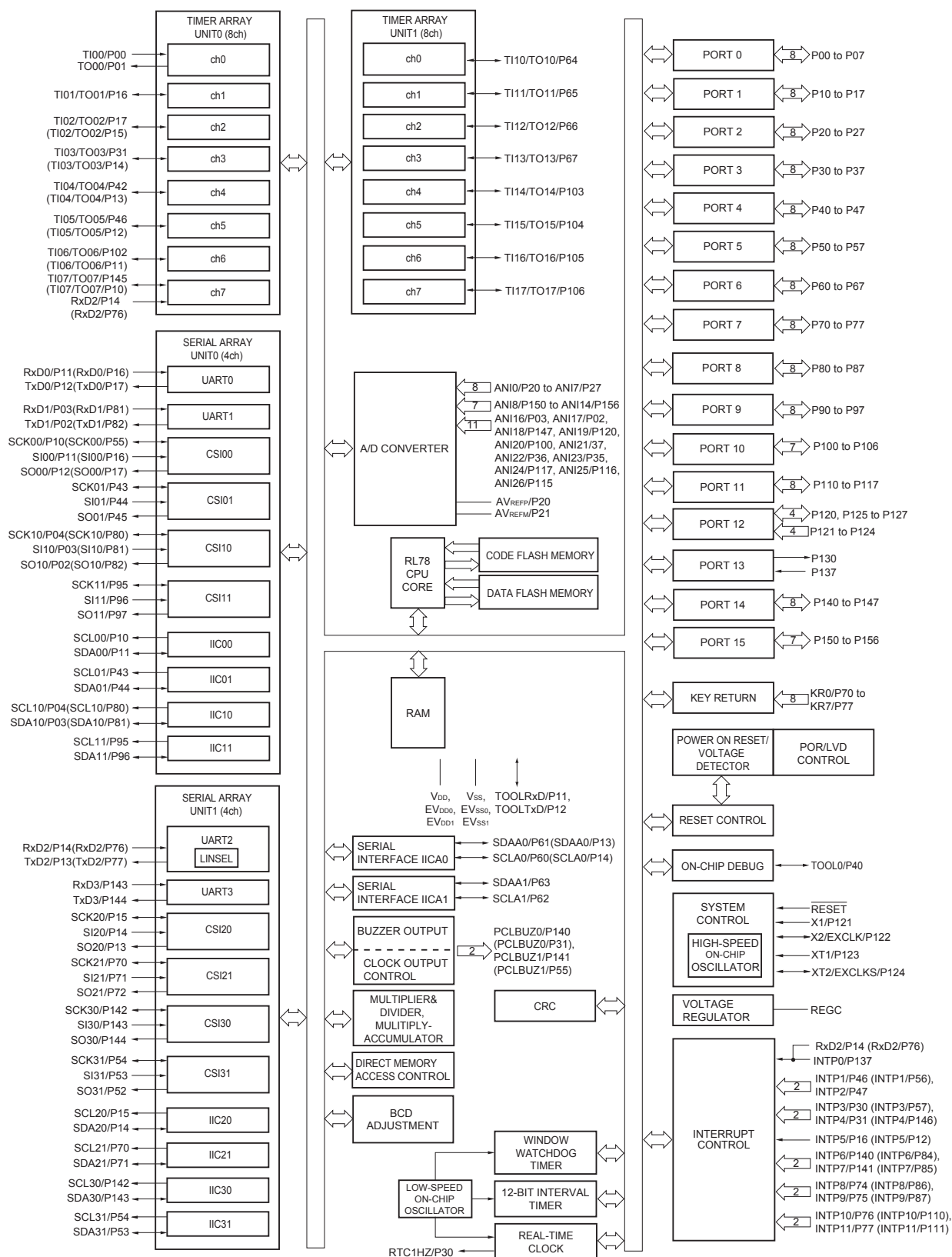
- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



- Cautions**
1. Make EV_{SS0}, EV_{SS1} pins the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0}, EV_{DD1} pins (EV_{DD0} = EV_{DD1}).
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μ F).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the V_{SS}, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		20-pin		24-pin		25-pin		30-pin		32-pin		36-pin	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash memory (KB)		16 to 64		16 to 64		16 to 64		16 to 128		16 to 128		16 to 128	
Data flash memory (KB)		4	—	4	—	4	—	4 to 8	—	4 to 8	—	4 to 8	—
RAM (KB)		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 4 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}		2 to 12 ^{Note1}	
Address space		1 MB											
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)											
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)											
Subsystem clock		—											
Low-speed on-chip oscillator		15 kHz (TYP.)											
General-purpose registers		(8-bit register × 8) × 4 banks											
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)											
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)											
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.											
I/O port	Total	16	20	21	26	28	32						
	CMOS I/O	13 (N-ch O.D. I/O [V _{DD} withstand voltage]: 5)	15 (N-ch O.D. I/O [V _{DD} withstand voltage]: 6)	15 (N-ch O.D. I/O [V _{DD} withstand voltage]: 6)	21 (N-ch O.D. I/O [V _{DD} withstand voltage]: 9)	22 (N-ch O.D. I/O [V _{DD} withstand voltage]: 9)	26 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)						
	CMOS input	3	3	3	3	3	3						
	CMOS output	—	—	1	—	—	—						
	N-ch O.D. I/O (withstand voltage: 6 V)	—	2	2	2	3	3						
Timer	16-bit timer	8 channels											
	Watchdog timer	1 channel											
	Real-time clock (RTC)	1 channel ^{Note 2}											
	12-bit interval timer (IT)	1 channel											
	Timer output	3 channels (PWM outputs: 2 ^{Note 3})	4 channels (PWM outputs: 3 ^{Note 3})			4 channels (PWM outputs: 3 ^{Note 3}), 8 channels (PWM outputs: 7 ^{Note 3}) ^{Note 4}							
	RTC output	—											

- Notes**
- The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.
R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H
R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.
 - Only the constant-period interrupt function when the low-speed on-chip oscillator clock (f_{IL}) is selected

(5) During communication at same potential (simplified I²C mode) (1/2)(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f _{SCL}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns
Hold time when SCLr = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(5) During communication at same potential (simplified I²C mode) (2/2)(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	t _{SU:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	1/f _{MCK} + 85 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 230 Note2		1/f _{MCK} + 230 Note2		1/f _{MCK} + 230 Note2		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		1/f _{MCK} + 290 Note2		1/f _{MCK} + 290 Note2		ns
Data hold time (transmission)	t _{HD:DAT}	2.7 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	—		0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)**

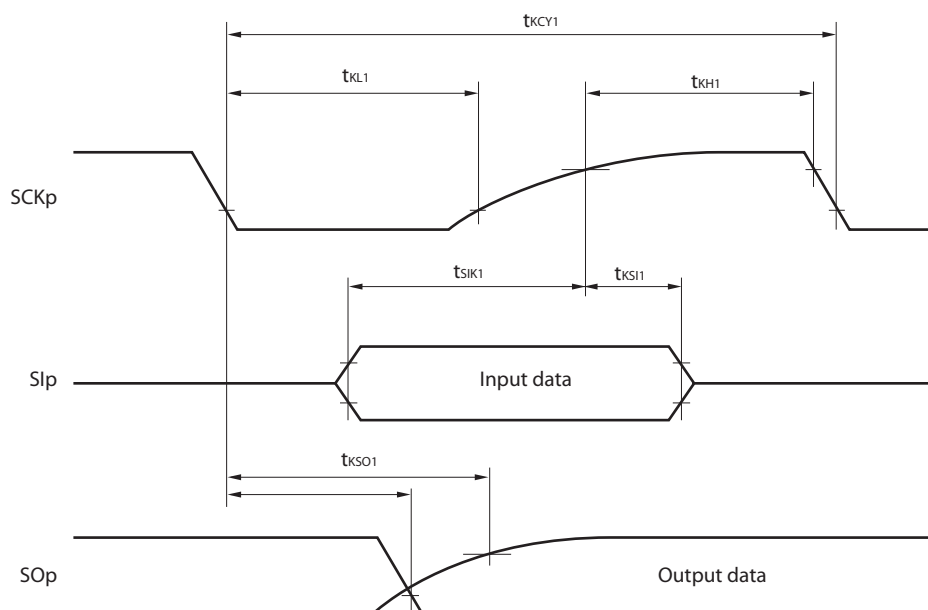
Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Transfer rate		Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
						5.3		1.3		0.6	Mbps
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}								
						5.3		1.3		0.6	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V			f _{MCK} /6 Note 1		f _{MCK} /6 Note 1		f _{MCK} /6 Note 1	bps
						5.3		1.3		0.6	Mbps
1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			f _{MCK} /6 Notes 1 to 3		f _{MCK} /6 Notes 1, 2		f _{MCK} /6 Notes 1, 2	bps			
			5.3		1.3		0.6	Mbps			
Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 4}											

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.**2.** Use it with EV_{DD0} ≥ V_b.**3.** The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}.2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps**4.** The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

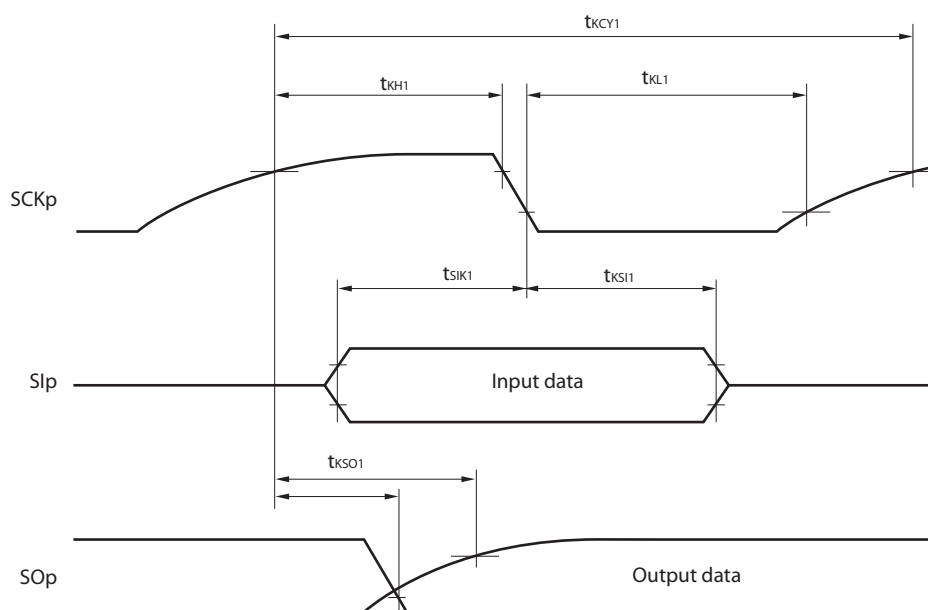
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage**2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)**3.** f_{MCK}: Serial array unit operation clock frequency(Operation clock to be set by the CKS_{mn} bit of serial mode register mn (SMR_{mn}). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))**4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks**
1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to $+105^\circ\text{C}$)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^\circ\text{C}$
R5F100xxGxx

- Cautions 1.** The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- 2.** With products not provided with an EV_{DD0} , EV_{DD1} , EV_{SS0} , or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD} , or replace EV_{SS0} and EV_{SS1} with V_{SS} .
- 3.** The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
- 4.** Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^\circ\text{C}$ to $+105^\circ\text{C}$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to $+85^\circ\text{C}$, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS ($T_A = -40$ to $+85^\circ\text{C}$)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^\circ\text{C}$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	$T_A = -40$ to $+85^\circ\text{C}$	$T_A = -40$ to $+105^\circ\text{C}$
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$ LS (low-speed main) mode: $1.8\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }8\text{ MHz}$ LV (low-voltage main) mode: $1.6\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }4\text{ MHz}$	HS (high-speed main) mode only: $2.7\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$ $2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
High-speed on-chip oscillator clock accuracy	$1.8\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C $1.6\text{ V} \leq \text{V}_{\text{DD}} < 1.8\text{ V}$ $\pm 5.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 5.5\% @ T_A = -40$ to -20°C	$2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$ $\pm 2.0\% @ T_A = +85$ to $+105^\circ\text{C}$ $\pm 1.0\% @ T_A = -20$ to $+85^\circ\text{C}$ $\pm 1.5\% @ T_A = -40$ to -20°C
Serial array unit	UART CSI: $f_{\text{CLK}}/2$ (supporting 16 Mbps), $f_{\text{CLK}}/4$ Simplified I ² C communication	UART CSI: $f_{\text{CLK}}/4$ Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter is in operation.
7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1} , I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
8. Current flowing only during data flash rewrite.
9. Current flowing only during self programming.
10. For shift time to the SNOOZE mode, see **18.3.3 SNOOZE mode** in the RL78/G13 User's Manual.

- Remarks**
1. f_{IL} : Low-speed on-chip oscillator clock frequency
 2. f_{SUB} : Subsystem clock frequency (XT1 clock oscillation frequency)
 3. f_{CLK} : CPU/peripheral hardware clock frequency
 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}\text{C}$

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	250		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V	t _{KCY1} /2 – 24		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	t _{KCY1} /2 – 36		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V	t _{KCY1} /2 – 76		ns
Slp setup time (to SCKp↑) ^{Note 1}	t _{SIK1}	4.0 V ≤ EV _{DD0} ≤ 5.5 V	66		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	66		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V	113		ns
Slp hold time (from SCKp↑) ^{Note 2}	t _{KSI1}		38		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	t _{KSO1}	C = 30 pF ^{Note 4}		50	ns

- Notes**
1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$ and $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

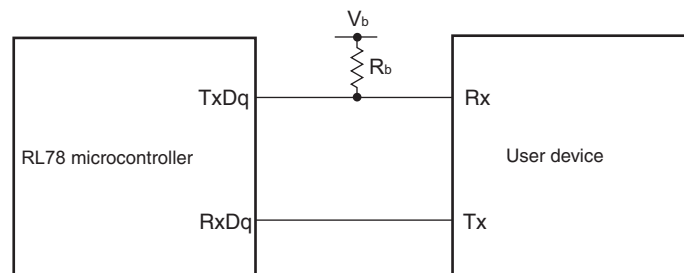
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

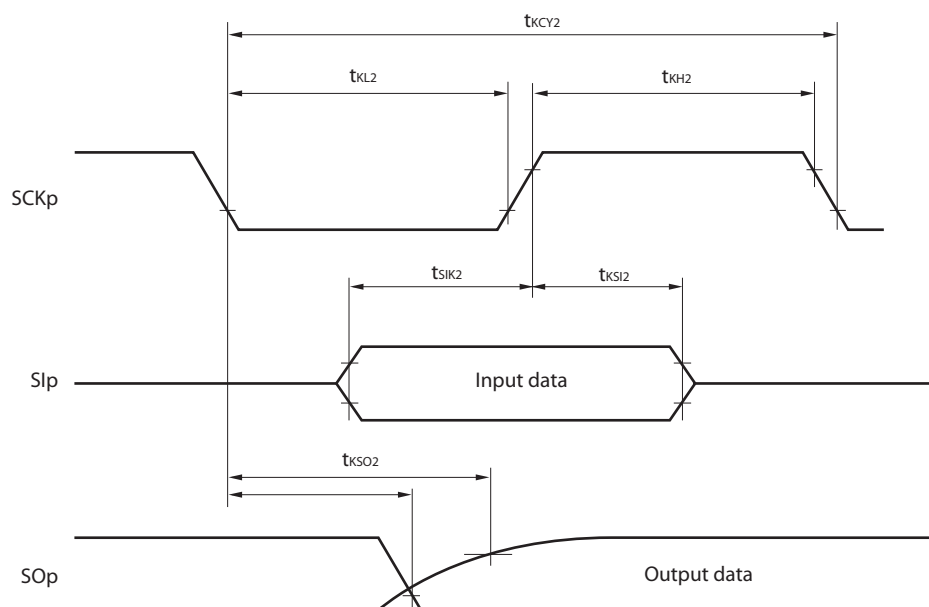
6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

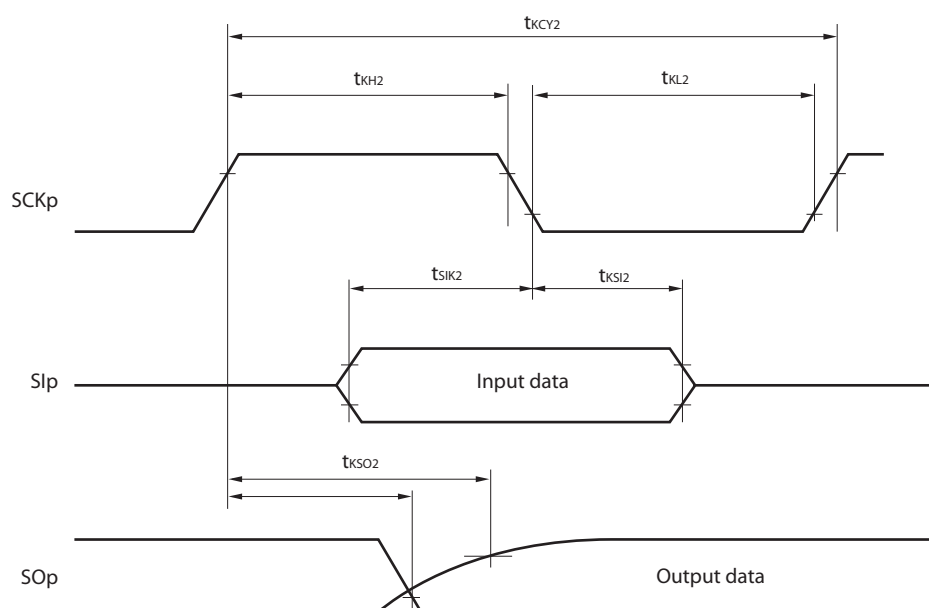
UART mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,
 n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
- 2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential.
 Use other CSI for communication at different potential.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Data setup time (reception)	$t_{\text{SU:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 340$ Note 2		ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	$1/f_{\text{MCK}} + 760$ Note 2		ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	$1/f_{\text{MCK}} + 570$ Note 2		ns
Data hold time (transmission)	$t_{\text{HD:DAT}}$	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	770	ns
		$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq \text{V}_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	0	1420	ns
		$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$, $2.3\text{ V} \leq \text{V}_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	0	1420	ns
		$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 3.3\text{ V}$, $1.6\text{ V} \leq \text{V}_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	0	1215	ns

Notes 1. The value must also be equal to or less than $f_{\text{MCK}}/4$.2. Set the f_{MCK} value to keep the hold time of $\text{SCLr} = \text{"L"}$ and $\text{SCLr} = \text{"H"}$.

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/ EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL} , see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 3}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 3}			V

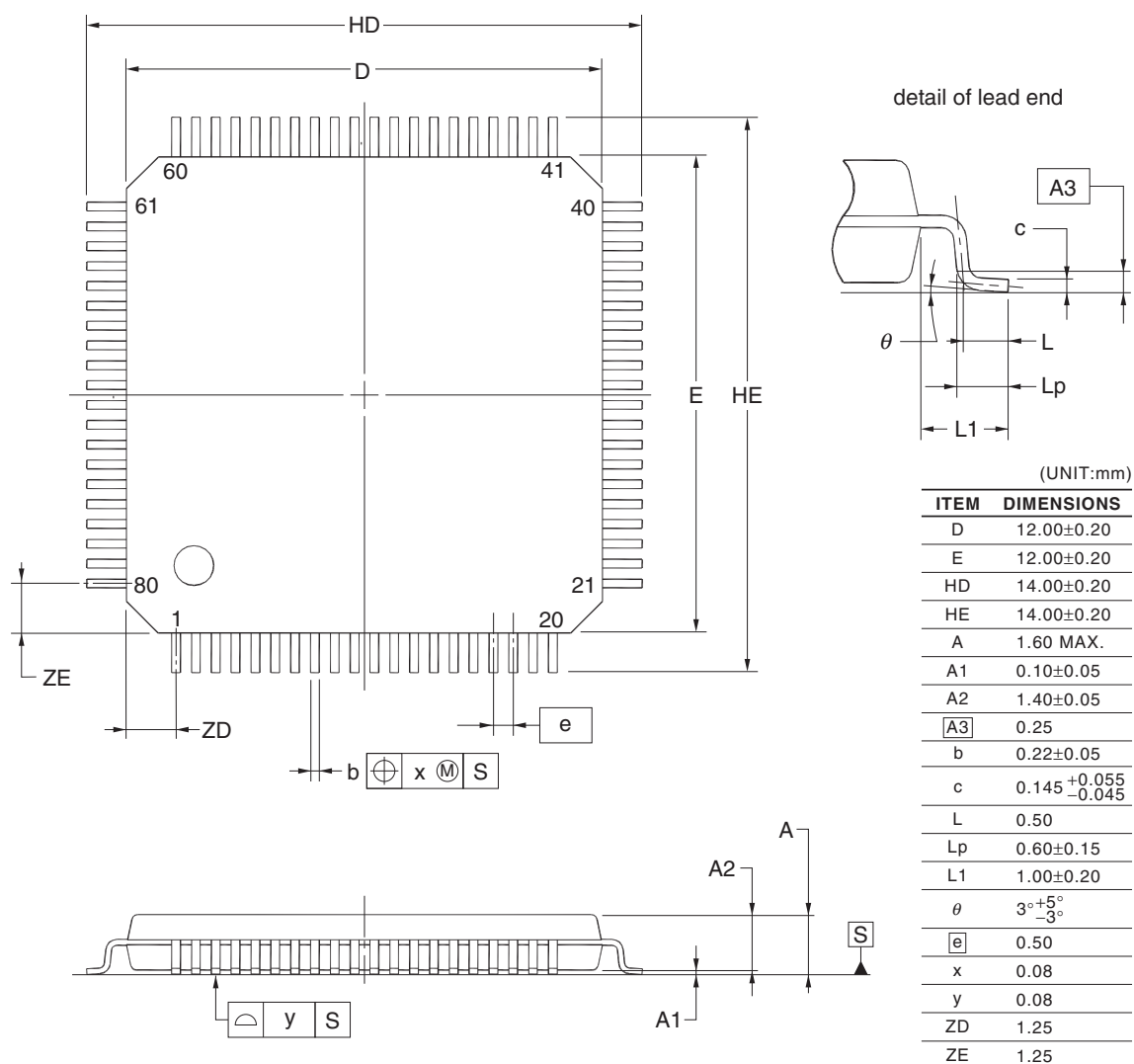
Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB
 R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB
 R5F100MFDDB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB
 R5F101MFDDB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB
 R5F100MFGFB, R5F100MGGB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

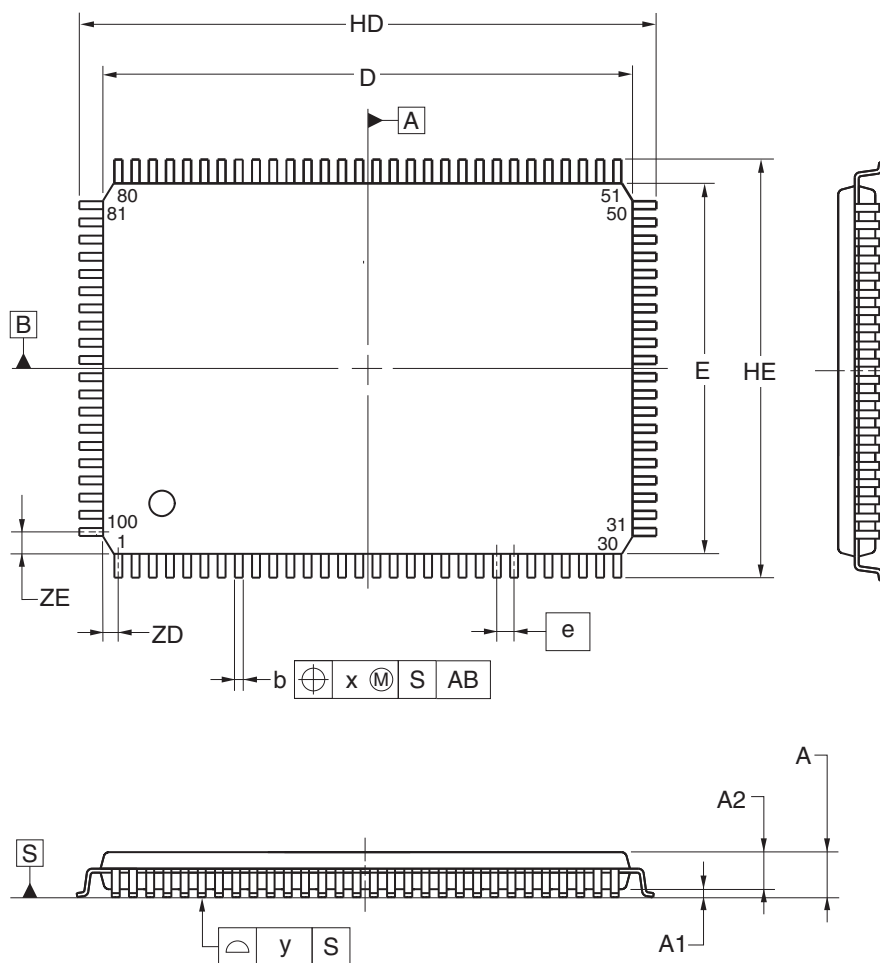
**NOTE**

Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

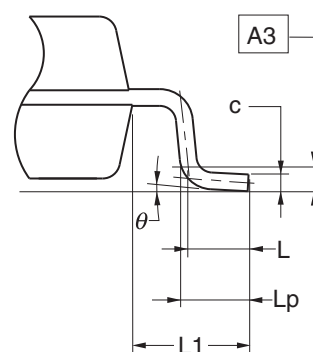
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R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAF, R5F100PKAFA, R5F100PLAFA
 R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAF, R5F101PKAFA, R5F101PLAFA
 R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F100PLDFA
 R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA
 R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.32 ^{+0.08} _{-0.07}
c	0.145 ^{+0.055} _{-0.045}
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	3° ^{+5°} _{-3°}
e	0.65
x	0.13
y	0.10
ZD	0.575
ZE	0.825